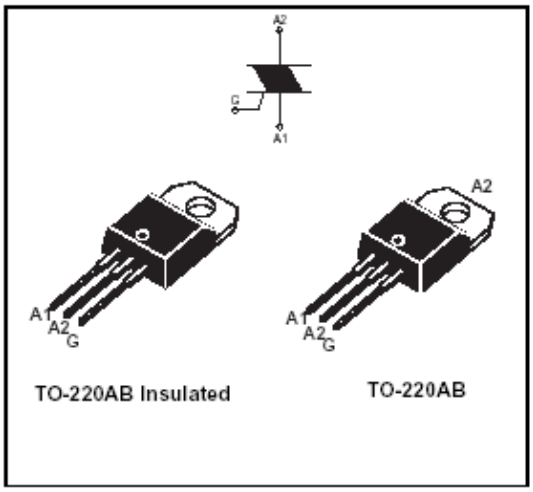
BTA/BTB08(8A TRIACS)

MAIN FEATURES:

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
V_{DRM}/V_{RRM}	600 and 800	V
$I_{G(Q1)}$	5 to 50	mA



ABSOLUTE RATING

Symbol	Parameter			Value	Units
$I_{T(RMS)}$	RMS on-state current(full sine wave)	TO-220AB	T_C=110℃	8	A
		TO-220AB Ins.	T_C=100℃		
I_{TSM}	Non-repetive peak on-state current (T_j=25℃, full cycle)	F=50Hz	t=20ms	80	A
		F=60Hz	t=16.7ms	84	
dI/dt	Critical rate of rise of on-state current I_G=2×I_{GT}, tr≤100ns	F=120Hz	T_j=125℃	50	A/μs
I_{GM}	Peak gate current	tp=20μs	T_j=125℃	4	A
$P_{G(AV)}$	Average gate power dissipation		T_j=125℃	1	W
T_{stg}	Storage junction temperature range			-40～150	℃
T_j	Operating junction temperature range			-40～150	℃

THERMAL RESISTANCE

Symbol	Parameter		Value	Unit
Rth(j-c)	Junction to case	TO-220AB	1.6	℃/W
		TO-220AB Ins.	2.5	
Rth(j-a)	Junction to ambient	TO-220AB	60	℃/W
		TO-220AB Ins.		

ELECTRICAL CHARACTERISTICS (T_j=25℃ unless otherwise stated)

Symbol	Testing conditions		Quadrant		Suffix						Unit
					TW	SW	CW	BW	C	B	
I_{GT}	V_D=12V, R_L=30Ω		Ⅰ-Ⅱ-Ⅲ	Max	5	10	35	50	25	50	mA
			Ⅳ		-	-	-	-	50	100	
V_{GT}			ALL	Max	1.3						V
V_{GD}	V_D=V_{DRM}, R_L=3.3KΩ, T_j=125℃		ALL	Min	0.2						V
I_L	I_G=1.2I_{GT}		Ⅰ-Ⅲ	Max	10	25	50	70	40	50	mA
			Ⅱ		15	30	60	80	80	100	
I_H	I_T=100mA		ALL	Max	10	15	35	50	-	-	mA
	I_T=500mA				-	-	-	-	25	50	
V_{TM}	I_T=11A, t=380μs		ALL	Max	1.55						V
I_{DRM} I_{RRM}	V_{DRM}=V_{RRM}	T_j=25℃		Max	5						μA
		T_j=125℃			1						mA
dv/dt	V_D=67% V_{DRM} Gate open T_j=125℃			Min	20	40	400	1000	200	400	V/μs